

PSMN3R9-25MLC

N-channel 25 V 4.15 mΩ logic level MOSFET in LFPAK33 using NextPower Technology

Rev. 4 — 15 June 2012

Product data sheet

Ultra low QG, QGD, & QOSS for high

system efficiencies at low and high

Synchronous buck regulator

Product profile 1.

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK33 package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

loads

1.2 Features and benefits

- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology

1.3 Applications

- DC-to-DC converters
- Load switching

| | 1.4 Quick refere | ence data | | | | |
|---------------------|----------------------------------|--------------------------------------------------------------------------------------------------------------------------|--------------|------|------|------|
| Table 1. | Quick reference data | | | | | |
| Symbol | Parameter | Conditions | Min | Тур | Мах | Unit |
| V_{DS} | drain-source voltage | $T_j = 25^{\circ}C$ | - | - | 25 | V |
| I _D | drain current | $T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{10000000000000000000000000000000000$ | <u>[1]</u> _ | - | 70 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | - | - | 69 | W |
| Т _ј | junction temperature | | -55 | - | 175 | °C |
| Static cha | aracteristics | | | | | |
| R_{DSon} | drain-source on-state resistance | V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 10</u> | - | 4.85 | 5.55 | mΩ |
| | | V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 10</u> | - | 3.65 | 4.15 | mΩ |
| Dynamic | characteristics | | | | | |
| Q_{GD} | gate-drain charge | V_{GS} = 4.5 V; I_D = 25 A; V_{DS} = 12.5 V; see <u>Figure 12</u> ; see <u>Figure 13</u> | - | 2.3 | - | nC |
| Q _{G(tot)} | total gate charge | V_{GS} = 4.5 V; I_D = 25 A; V_{DS} = 12.5 V; see Figure 12; see Figure 13 | - | 9.7 | - | nC |

[1] Continuous current is limited by package.

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2. Pinning information

| Table 2. | Pinning | j information | | | |
|----------|---------|-----------------------------------|--------------------|----------------|--|
| Pin | Symbol | Description | Simplified outline | Graphic symbol | |
| 1 | S | source | | - | |
| 2 | S | source | | | |
| 3 | S | source | | | |
| 4 | G | gate | | | |
| mb | D | mounting base; connected to drain | | mbb076 S | |
| | | | SOT1210 (LFPAK33) | | |

3. Ordering information

| Table 3. Ordering information | | | | | | | |
|-------------------------------|---------|--------------------------------------------------------------------|---------|--|--|--|--|
| Type number | Package | | | | | | |
| | Name | Description | Version | | | | |
| PSMN3R9-25MLC | LFPAK33 | Plastic single ended surface mounted package (LFPAK33); 4 leads | SOT1210 | | | | |

4. Limiting values

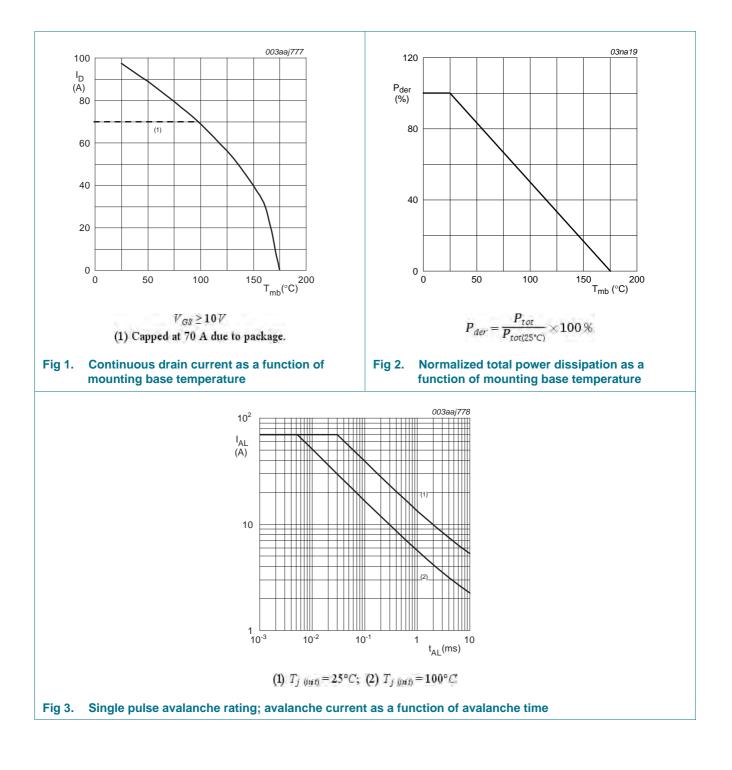
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Mi | n Max | Unit |
|----------------------|-------------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------|-------|------|
| - | | | | | |
| V _{DS} | drain-source voltage | $T_j = 25^{\circ}C$ | - | 25 | V |
| V _{GS} | gate-source voltage | | -20 |) 20 | V |
| I _D | drain current | V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u> | <u>[1]</u> _ | 70 | А |
| | | V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u> | - | 69 | А |
| I _{DM} | peak drain current | pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C; see <u>Figure 4</u> | - | 390 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | - | 69 | W |
| T _{stg} | storage temperature | | -5 | 5 175 | °C |
| Tj | junction temperature | | -5 | 5 175 | °C |
| T _{sld(M)} | peak soldering temperature | | - | 260 | °C |
| V _{ESD} | electrostatic discharge voltage | MM (JEDEC JESD22-A115) | 23 | 0 - | V |
| Source-drain | diode | | | | |
| I _S | source current | T _{mb} = 25 °C | - | 63 | А |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | - | 390 | А |
| Avalanche rug | gedness | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | $ \begin{array}{l} V_{GS} = 10 \text{ V}; \ T_{j(init)} = 25 \ ^{\circ}\text{C}; \ I_{D} = 70 \text{ A}; \\ V_{sup} \leq 25 \text{ V}; \ R_{GS} = 50 \ \Omega; \ unclamped; \\ see \ \overline{Figure \ 3} \end{array} $ | - | 34.5 | mJ |

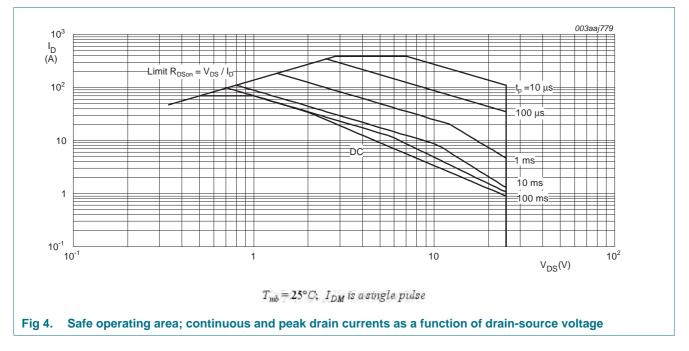
[1] Continuous current is limited by package.

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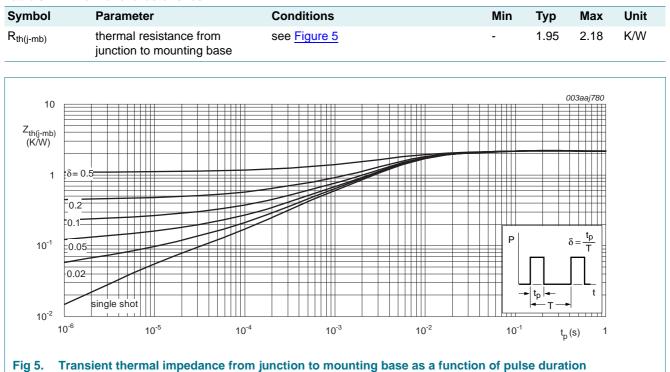
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5. Thermal characteristics

Table 5.Thermal characteristics



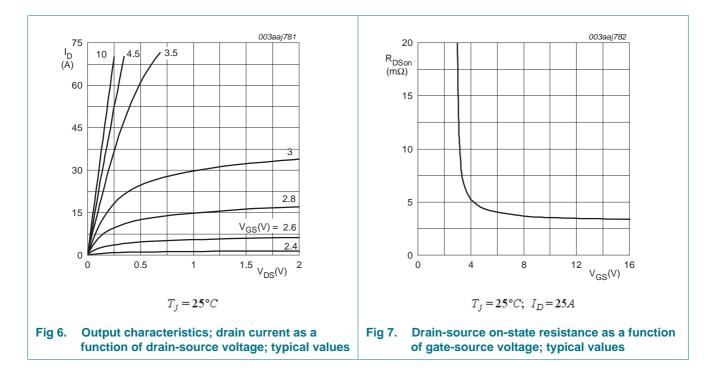
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6. Characteristics

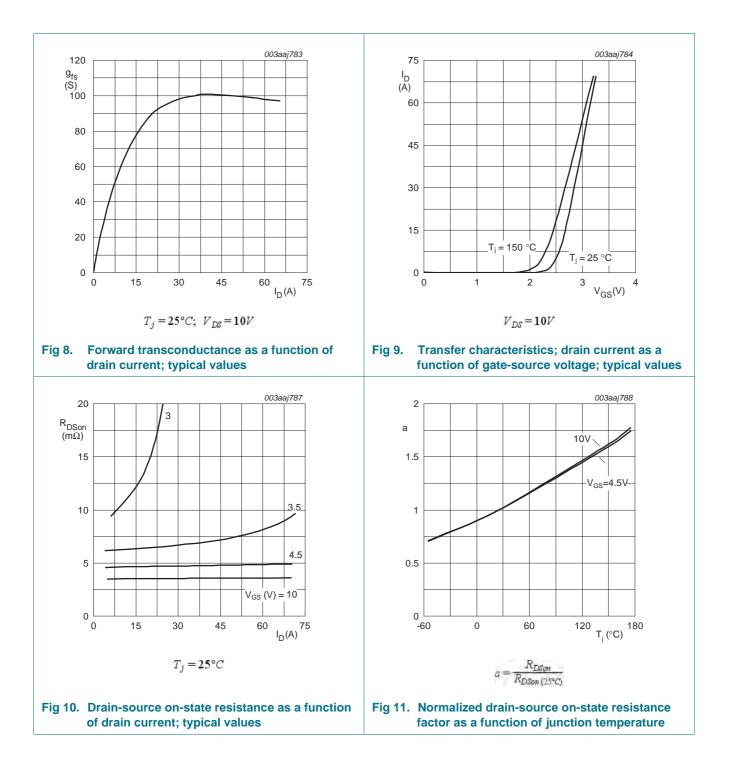
| Table 6. Cl | haracteristics | | | | | |
|--------------------------------|----------------------------------------------------------------|------------------------------------------------------------------------------------------------------------------------|------|------|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static charac | teristics | | | | | |
| V _{(BR)DSS} | drain-source | I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C | 25 | - | - | V |
| | breakdown voltage | $I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$ | 22.5 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C | 1.45 | 1.81 | 2.15 | V |
| $\Delta V_{GS(th)} / \Delta T$ | gate-source threshold voltage variation with temperature | | - | -4.1 | - | mV/K |
| I _{DSS} | drain leakage current | V_{DS} = 25 V; V_{GS} = 0 V; T_j = 25 °C | - | - | 1 | μΑ |
| | | V_{DS} = 25 V; V_{GS} = 0 V; T_j = 150 °C | - | - | 100 | μA |
| I _{GSS} | gate leakage current | V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C | - | - | 100 | nA |
| | | V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C | - | - | 100 | nA |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 10</u> | - | 4.85 | 5.55 | mΩ |
| | | V_{GS} = 4.5 V; I_D = 25 A; T_j = 150 °C; see <u>Figure 10</u> ; see <u>Figure 11</u> | - | - | 8.9 | mΩ |
| | | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 10</u> | - | 3.65 | 4.15 | mΩ |
| | | V _{GS} = 10 V; I _D = 25 A; T _j = 150 °C; see <u>Figure 10</u> ; see <u>Figure 11</u> | - | - | 6.65 | mΩ |
| R _G | gate resistance | f = 1 MHz | 0.9 | 1.8 | 3.6 | Ω |
| Dynamic cha | racteristics | | | | | |
| Q _{G(tot)} | total gate charge | $I_D = 25 \text{ A}; V_{DS} = 12.5 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 12</u> ; see <u>Figure 13</u> | - | 21.5 | - | nC |
| | | $I_D = 25 \text{ A}; V_{DS} = 12.5 \text{ V}; V_{GS} = 4.5 \text{ V};$ see <u>Figure 12</u> ; see <u>Figure 13</u> | - | 9.7 | - | nC |
| | | $I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$ | - | 20.9 | - | nC |
| Q _{GS} | gate-source charge | $I_D = 25 \text{ A}; V_{DS} = 12.5 \text{ V}; V_{GS} = 4.5 \text{ V};$ | - | 3.9 | - | nC |
| Q _{GS(th)} | pre-threshold gate-source charge | see <u>Figure 12</u> ; see <u>Figure 13</u> | - | 2.4 | - | nC |
| Q _{GS(th-pl)} | post-threshold gate-source charge | | - | 1.5 | - | nC |
| Q _{GD} | gate-drain charge | | - | 2.3 | - | nC |
| V _{GS(pl)} | gate-source plateau voltage | I_D = 25 A; V_{DS} = 12.5 V; see <u>Figure 12</u> ; see <u>Figure 13</u> | - | 2.9 | - | V |
| C _{iss} | input capacitance | V _{DS} = 12.5 V; V _{GS} = 0 V; f = 1 MHz; | - | 1524 | - | pF |
| C _{oss} | output capacitance | $T_j = 25 \text{ °C}; \text{ see } Figure 14$ | - | 376 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 128 | - | pF |

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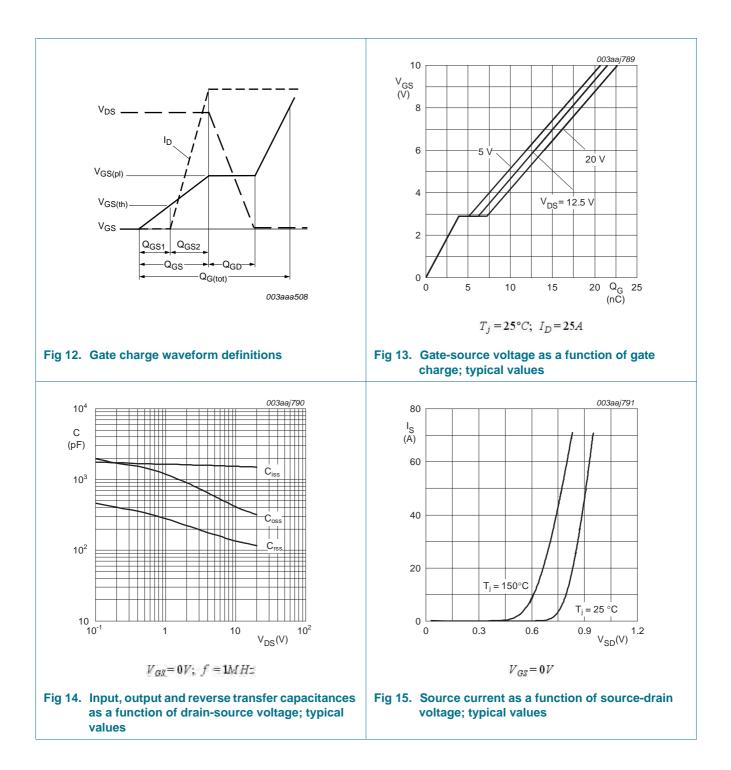
| Table 6. | Characteristics continued | | | | | |
|---------------------|----------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------|-----|------|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| t _{d(on)} | turn-on delay time | V_{DS} = 12.5 V; R_L = 0.5 $\Omega;$ V_{GS} = 4.5 V; | - | 13 | - | ns |
| t _r | rise time | $R_{G(ext)} = 5 \Omega$ | - | 23.2 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 15.6 | - | ns |
| t _f | fall time | | - | 9.8 | - | ns |
| Q _{oss} | output charge | $V_{GS} = 0 \text{ V}; V_{DS} = 12.5 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$ | - | 9.9 | - | nC |
| Source-dra | in diode | | | | | |
| V _{SD} | source-drain voltage | I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 15</u> | - | 0.82 | 1.1 | V |
| t _{rr} | reverse recovery time | $I_{S} = 25 \text{ A}; \text{dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{V}_{GS} = 0 \text{ V};$ | - | 17.6 | - | ns |
| Q _r | recovered charge | V _{DS} = 12.5 V | - | 9.2 | - | nC |
| t _a | reverse recovery rise time | $V_{GS} = 0 \text{ V}; I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$ $V_{DS} = 12.5 \text{ V}; \text{ see } \frac{\text{Figure } 16}{16}$ | - | 9.8 | - | ns |
| t _b | reverse recovery fall time | | - | 7.8 | - | ns |



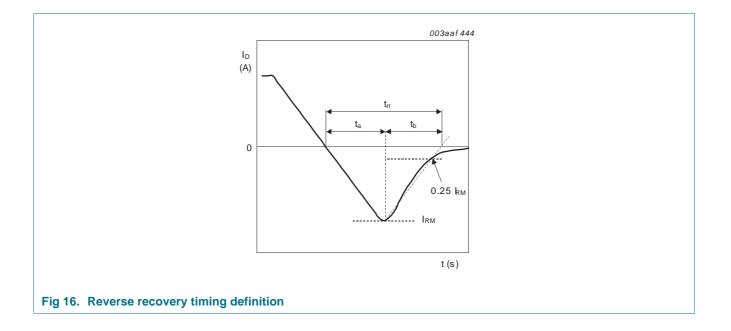
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7. Package outline

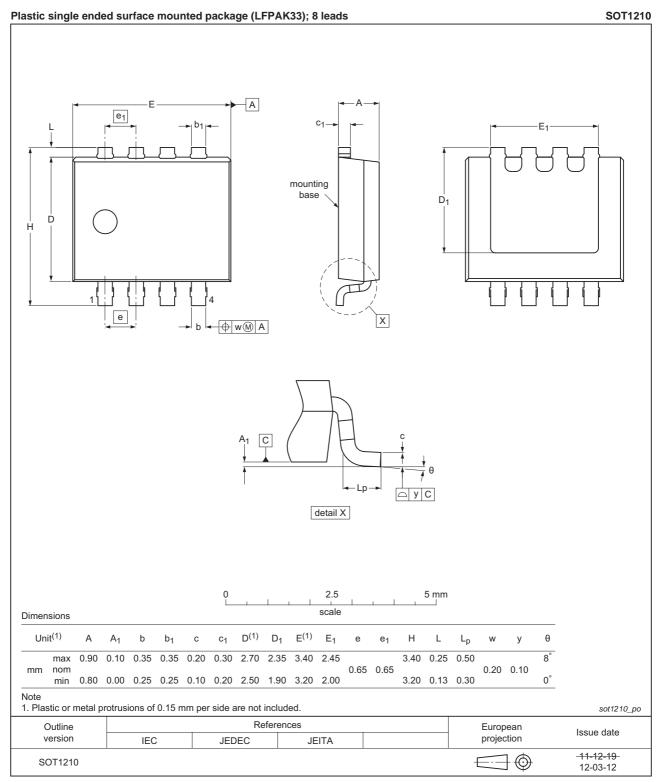


Fig 17. Package outline SOT1210 (LFPAK33)

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8. Revision history

| Document ID Release date | | Data sheet status | Change notice | Supersedes |
|--------------------------|----------------------------------------|--------------------|---------------|-------------------|
| PSMN3R9-25MLC v.4 | 20120615 | Product data sheet | - | PSMN3R9-25MLC v.3 |
| Modifications: | Various changes to | o content. | | |
| PSMN3R9-25MLC v.3 | 20120607 | Product data sheet | - | PSMN3R9-25MLC v.2 |

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Legal information 9.

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| Document status[1] [2] | Product status ^[3] | Definition |
|--------------------------------|-------------------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions'

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PSMN3R9-25MLC

N-channel 25 V 4.15 mΩ logic level MOSFET in LFPAK33 using NextPower Technology

11. Contents

| 1 | Product profile1 |
|-----|--------------------------|
| 1.1 | General description1 |
| 1.2 | Features and benefits1 |
| 1.3 | Applications1 |
| 1.4 | Quick reference data1 |
| 2 | Pinning information2 |
| 3 | Ordering information2 |
| 4 | Limiting values2 |
| 5 | Thermal characteristics4 |
| 6 | Characteristics5 |
| 7 | Package outline10 |
| 8 | Revision history11 |
| 9 | Legal information12 |
| 9.1 | Data sheet status |
| 9.2 | Definitions12 |
| 9.3 | Disclaimers |
| 9.4 | Trademarks13 |
| 10 | Contact information13 |